

IN THE U.S. PATENT AND TRADEMARK OFFICE

In re application of: Yoshiaki HISAMUNE et al.

Appl. No.: NEW

Group:

Filed: February 27, 2002 Examiner:

For: METHOD OF MANUFACTURING SEMICONDUCTOR  
DEVICE, NONVOLATILE SEMICONDUCTOR MEMORY  
DEVICE AND METHOD OF MANUFACTURING THE  
SAME

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, DC 20231

February 27, 2002

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SPECIFICATION:

Page 19, replace third full paragraph as follows:

--Figs. 33A and 33B are a series of cross-sectional views of the conventional nonvolatile semiconductor memory device, illustrating the order of processing steps of the conventional method of manufacturing the conventional nonvolatile semiconductor memory device;--